

Title (en)
Semiconductor device and method of producing the same

Title (de)
Halbleiteranordnung und dessen Herstellungsverfahren

Title (fr)
Dispositif semi-conducteur et son procédé de fabrication

Publication
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Application
EP 99119612 A 19991004

Priority
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Abstract (en)
[origin: EP1024532A2] A semiconductor device and a method of producing the same are provided. The semiconductor device includes a semiconductor chip, a die pad onto which the semiconductor chip is mounted via a die bonding material, and a resin package which seals at least the semiconductor chip and the die pad. The die pad is provided with bond reinforcing members each including a penetrating portion and a step portion. The step portion is formed within the range of the thickness of the die pad. With the semiconductor chip being mounted on the die pad, spaces are formed between the semiconductor chip and the step portion, and part of the resin package is interposed in the spaces. <IMAGE>

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Citation (search report)
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